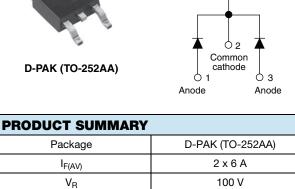
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Schottky Rectifier, 2 x 6 A



Base common cathode

04

0.65 V

4 mA at 125 °C

150 °C

Common cathode

6 mJ

FEATURES

- Popular D-PAK outline
- Center tap configuration
- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability

VS-12CWQ10FNPbF

- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 $^\circ\text{C}$

DESCRIPTION

The VS-12CWQ10FNPbF surface mount, center tap, Schottky rectifier series has been designed for applications requiring low forward drop and small foot prints on PC board. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS									
SYMBOL	CHARACTERISTICS	VALUES	UNITS						
I _{F(AV)}	Rectangular waveform	12	А						
V _{RRM}		100	V						
I _{FSM}	t _p = 5 μs sine	330	А						
V _F	6 Apk, T _J = 125 °C (per leg)	0.65	V						
TJ	Range	- 55 to 150	°C						

VOLTAGE RATINGS									
PARAMETER	SYMBOL	VS-12CWQ10FNPbF	UNITS						
Maximum DC reverse voltage	V _R	100	V						
Maximum working peak reverse voltage	V _{RWM}	100	v						

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDI	VALUES	UNITS					
Maximum average per leg		50 % duty cycle at T _C = 135 °C	6	A					
See fig. 5 per device	I _{F(AV)}	50% duty cycle at $T_{\rm C} = 135\%$ C	12						
Maximum peak one cycle		5 µs sine or 3 µs rect. pulse	Following any rated load condition and with	330	A				
non-repetitive surge current per leg See fig. 7	IFSM	10 ms sine or 6 ms rect. pulse	rated V_{RRM} applied	110					
Non-repetitive avalanche energy per leg	E _{AS}	T _J = 25 °C, I _{AS} = 1 A, L = 12 mH		6	mJ				
Repetitive avalanche current per leg	I _{AR}	Current decaying linearly to zero in 1 μ s Frequency limited by T _J maximum V _A = 1.5 x V _R typical		1	А				





 V_F at I_F

 I_{RM}

T_J max.

Diode variation

E_{AS}

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ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST C	VALUES	UNITS				
		6 A	T 05 %C	0.80				
Maximum forward	V _{FM} ⁽¹⁾	12 A	— T _J = 25 °C	0.95	V			
voltage drop per leg See fig. 1		6 A	T 105 %C	0.65				
		12 A	— T _J = 125 °C	0.78				
Maximum reverse leakage current per leg	I _{BM} ⁽¹⁾	T _J = 25 °C	$V_{\rm B}$ = Rated V _B	1	mA			
See fig. 2	IRM W	T _J = 125 °C	VR = naleu VR	4				
Threshold voltage	V _{F(TO)}		0.47	V				
Forward slope resistance	r _t	$T_J = T_J maximum$	20.68	mΩ				
Typical junction capacitance per leg	CT	$V_{R} = 5 V_{DC}$, (test signal r	183	pF				
Typical series inductance per leg	L _S	Measured lead to lead 5	5.0	nH				

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,$ duty cycle < 2 $\,\%$

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range		T_{J} ⁽¹⁾ , T_{Stg}		- 55 to 150	°C			
Maximum thermal resistance,	per leg	Р	DC operation	3.0	°C/W			
junction to case	per device	R _{thJC}	See fig. 4	1.5				
Approximate weight				0.3	g			
				0.01	oz.			
Marking device			Case style D-PAK (similar to TO-252AA)	12CW0	210FN			

Note

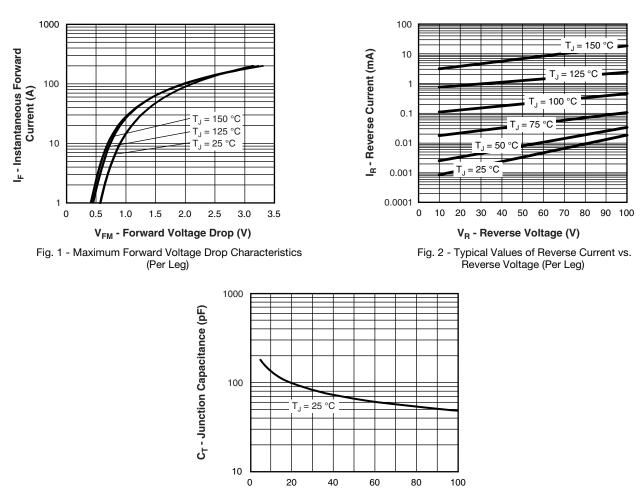
(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink



VS-12CWQ10FNPbF

Schottky Rectifier, 2 x 6 A

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V_R - Reverse Voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

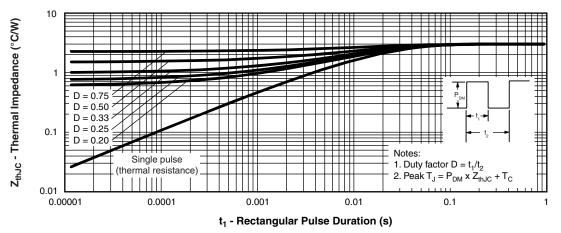


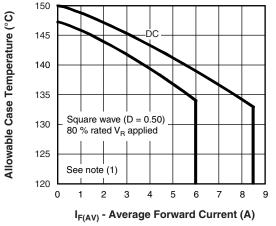
Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

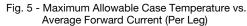
VS-12CWQ10FNPbF

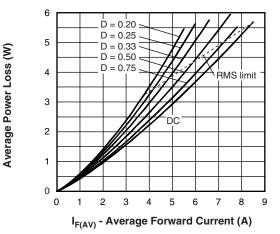
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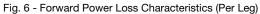
Schottky Rectifier, 2 x 6 A











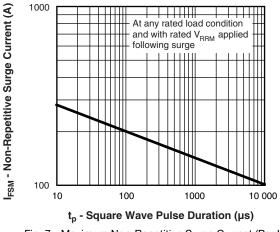


Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

Note

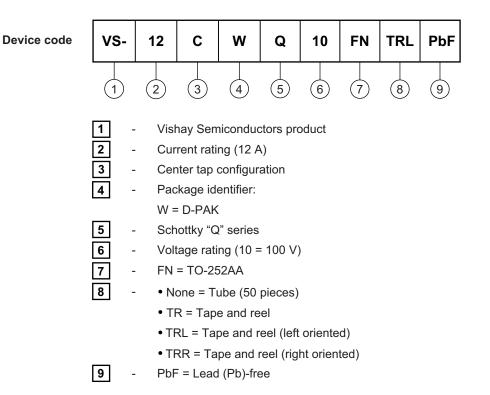
- Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$; (1)
 - $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$



Schottky Rectifier, 2 x 6 A

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ORDERING INFORMATION TABLE



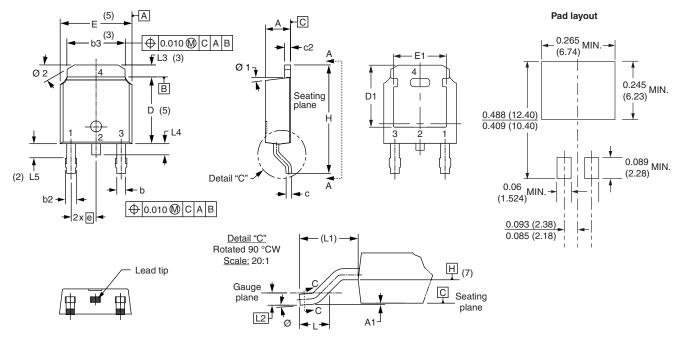
LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95016						
Part marking information	www.vishay.com/doc?95059					
Packaging information	www.vishay.com/doc?95033					
SPICE model	www.vishay.com/doc?95177					



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D-PAK (TO-252AA)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES		SYMBOL	MILLIMETERS		INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIDUL	MIN.	MAX.	MIN.	MAX.	NUTES
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090) BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	BREF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	0.020	BSC	
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

⁽⁴⁾ Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC outline TO-252AA

Document Number: 95016



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